

**Amendments to the Claims:**

None

**Listing of Claims:**

Claim 1 (previously amended): An integrated circuit, comprising:  
at least one PNP bipolar transistor, comprising:  
an emitter diffusion which has a doping profile that combines a P-well and a P+ diffusion;  
a base diffusion comprising a N-well that at least partly underlies said emitter diffusion wherein  
said emitter and base diffusions jointly defining an emitter:base ratio of near-junction dopants, measured at 75% and 125% of the emitter-base junction depth, which is greater than two to one.

Claim 2 (canceled)

Claim 3 (previously amended). The integrated circuit of Claim 1 further comprising a blanket P-type diffusion component having a peak concentration depth more than twice that of said P-well.

Claims 4-8 (canceled)

Claim 9 (withdrawn): An integrated circuit fabrication method, comprising the steps of:  
(a) implanting p-type dopants into p-well locations and PNP emitter locations, but not into all locations;  
(b) implanting n-type dopants into n-well locations and PNP emitter locations, but not into all locations;

- (c) implanting p-type dopants into PMOS source/drain locations and PNP emitter locations, with a stopping distance less than half of that used in said step (a);  
and
  - (d) implanting p-type dopants overall, with a stopping distance more than twice that used in said step (c);
- whereby emitter efficiency of resulting PNP transistors is improved.